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Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

007 00 (70 000)



Marking code: 9K

PRODUCT SUMMARY				
V _{DS} (V)	40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0265			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.032			
I _D (A)	8			
Configuration	Single			
Package	SOT-23			

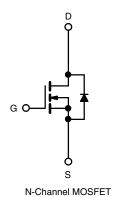
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unless	otherwise noted	d)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	40	V	
Gate-source voltage		V_{GS}	± 20	V	
Continuous drain current	T _C = 25 °C	1	8		
Continuous drain current	T _C = 125 °C	Ι _D	4.8		
Continuous source current (diode conduction)		Is	2.7	Α	
Pulsed drain current ^a		I _{DM}	32		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	8.5		
Single pulse avalanche energy	L = 0.1 IIII1	E _{AS}	3.6	mJ	
Maximum power dissipation ^a	T _C = 25 °C	Pn	3	w	
	T _C = 125 °C	ı D	1	VV	
Operating junction and storage temperature	range	T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB Mount b	R_{thJA}	166	°C/W
Junction-to-foot (drain)		R_{thJF}	50	C/VV

Notes

- a. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2~\%$
- b. When mounted on 1" square PCB (FR4 material)



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40	-	-	.,
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V
Gate-source leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1	V nA μA A Ω S PF nC Ω ns
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$	-	-	50	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	150	
On-state drain current a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	10	-	-	Α
		V _{GS} = 10 V	I _D = 4 A	-	0.021	0.0263	V nA μA A Ω S PF nC Ω
Drain agures on state registence 8	Б	V _{GS} = 10 V	I _D = 4 A, T _J = 125 °C	-	-	0.039	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 4 A, T _J = 175 °C	-	-	0.044	
		V _{GS} = 4.5 V	I _D = 3 A	-	0.025	0.032	
Forward transconductance b	9 _{fs}	V _{DS}	= 15 V, I _D = 5 A	-	21	-	S
Dynamic ^b							
Input capacitance	C _{iss}			-	358	500	
Output capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	135	190	рF
Reverse transfer capacitance	C _{rss}			-	17	24	
Total gate charge ^c	Qg			-	6.7	9.4	
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, I_{D} = 3 \text{ A}$	-	1.4	-	nC
Gate-drain charge ^c	Q_{gd}			- 21 - 358 500 - 135 190 - 17 24 - 6.7 9.4 - 1.4 - 1.1 - 2.8 7.1 11.3 - 7.8 11 - 3.7 5.2			
Gate resistance	R _g		f = 1 MHz	2.8	7.1	11.3	Ω
Turn-on delay time ^c	t _{d(on)}			-	7.8	11	
Rise time ^c	t _r			3.7	5.2	ns	
Turn-off delay time ^c	t _{d(off)}			15.6	22		
Fall time ^c	t _f	1		-	2.9	4.0	
Source-Drain Diode Ratings and Char	acteristics b						
Pulsed current ^a	I _{SM}			-	-	11	Α

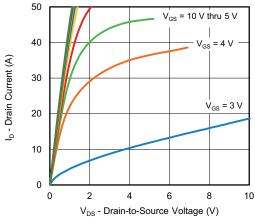
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

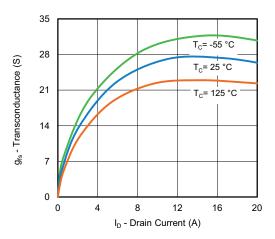
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



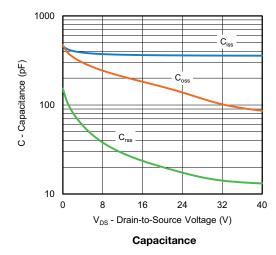
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

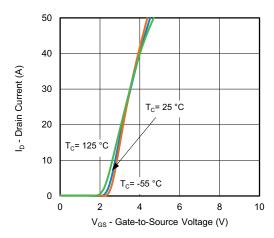




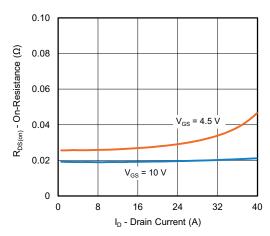


Transconductance

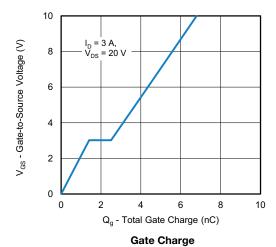




Transfer Characteristics

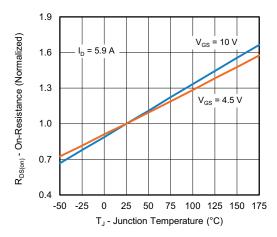


On-Resistance vs. Drain Current

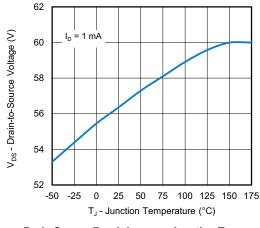




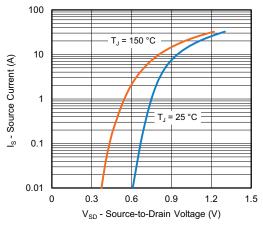
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



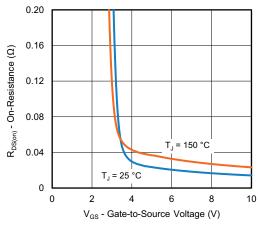
On-Resistance vs. Junction Temperature



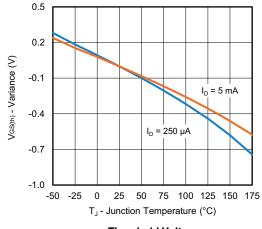
Drain Source Breakdown vs. Junction Temperature



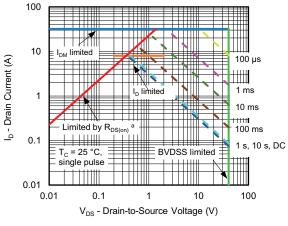
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Safe Operating Area

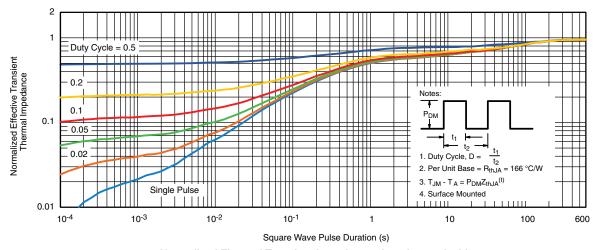
Note

a. V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

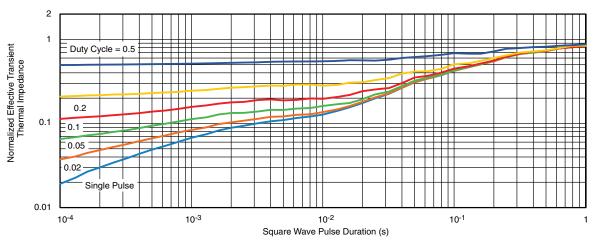
For technical questions, contact: automostechsu



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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SOT-23 (TO-236): 3-LEAD







Dim	MILLIN	METERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	

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RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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